

THE UNIVERSITY OF BRITISH COLUMBIA  
Department of Electrical and Computer Engineering  
ELEC301 – Electronic Circuits  
Midterm - October 20, 2025

Answer all problems.  
Time: 50 min.

**This examination consists of 9 pages. Please check that you have a complete copy. You may use both sides of each sheet if needed.**

#	MAX	GRADE
1	25	
2	25	
3	25	
4	25	
TOTAL	100	

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Surname

First

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Student Number

READ THIS

→ IMPORTANT NOTE: The announcement “stop writing” will be made at the end of the examination. Anyone writing after this announcement will receive a score of 0. No exceptions, no excuses.

*All writings must be on this booklet. The blank sides on the reverse of each page may also be used.*

*Each candidate should be prepared to produce, upon request, his/her Library/AMS card.*

*Read and observe the following rules:*

*No candidate shall be permitted to enter the examination room after the expiration of 15min, or to leave during the first 10min of the examination.*

*Candidates are not permitted to ask questions of the invigilator(s), except in cases of supposed errors or ambiguities in examination-questions.*

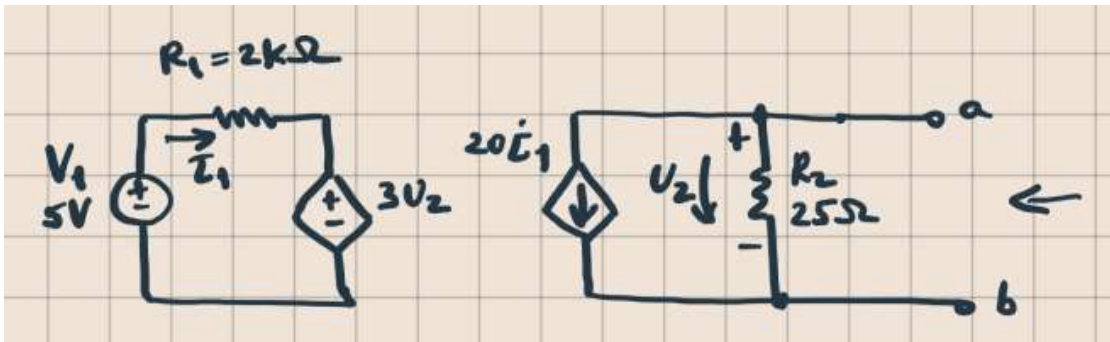
**Caution** - *Candidates guilty of any of the following, or similar, dishonest practices shall be immediately dismissed from the examination and shall be liable to disciplinary action:*

- *Making use of any books, papers or memoranda, calculators, audio or visual cassette players or other memory aid devices, other than as authorized by the examiners.*
- *Speaking or communicating with other candidates.*
- *Purposely exposing written papers to the view of other candidates.*

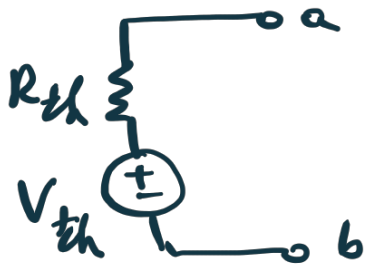
*The plea of accident or forgetfulness shall not be received.*

1) [25p]

Find the equivalent Thevenin representation with respect to the port a-b of the following circuit (pay attention to the dependent sources).



Sol: We want to reduce the circuit to



We firstly determine  $V_{th} = V_{ab}^{oc}$

$$\begin{cases} \dot{I}_1 = \frac{V_1 - 3V_2}{R_1} \\ V_2 = -R_2(20\dot{I}_1) \end{cases} \Rightarrow V_2 = -20R_2 \frac{V_1 - 3V_2}{R_1}$$

$$\Downarrow$$

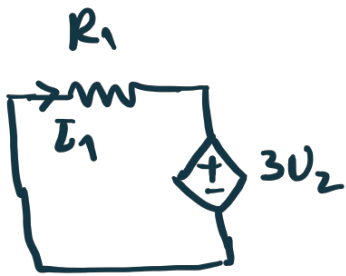
$$V_2 = -20 \frac{R_2}{R_1} V_1 + 60 \frac{R_2}{R_1} V_2$$

$$20 \frac{R_2}{R_1} V_1 = \left( \frac{60R_2}{R_1} - 1 \right) V_2$$

$$V_2 = V_{th} = \frac{20R_2/R_1}{\frac{60R_2}{R_1} - 1} V_1 = \frac{20R_2}{60R_2 - R_1} V_1$$

$$V_{th} = \frac{20 \cdot \cancel{25}}{60 \cdot \cancel{25} - \frac{2000}{80}} 5V = \frac{20}{-20} = -5V$$

For  $R_{th} \rightarrow$  we deactivate the independent voltage source



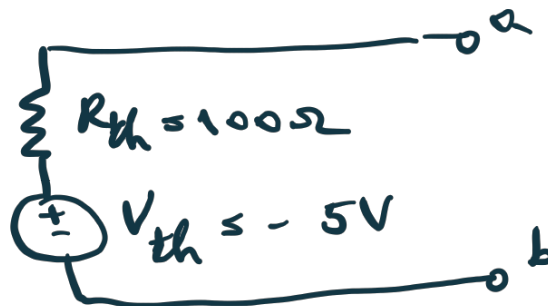
$$V_2 = V_t \Rightarrow \dot{I}_1 = -\frac{3V_t}{R_1}$$

$$\dot{I}_t = \frac{V_t}{R_2} + 20 \cdot \left( -\frac{3V_t}{R_1} \right) = V_t \left( \frac{1}{R_2} - \frac{60}{R_1} \right) \Rightarrow$$

$$\Rightarrow R_{th} = \frac{V_t}{\dot{I}_t} = \frac{1}{\frac{1}{R_2} - \frac{60}{R_1}} = \frac{1}{\frac{1}{25} - \frac{60}{2000}}$$

$$R_{th} = \frac{200}{8 - 6} \Omega = \frac{200}{2} \Omega = 100 \Omega$$

Concl



Grading: 25p total - 10p for  $V_{th}$  + 15p for  $R_{th}$

2) [25p] Given the following transfer function

$$H(s) = \frac{(s+10)(s+100)}{(s^2 + 1001s + 1000)(s+10000)(s+50000)}$$

- Sketch the Bode plots for both the magnitude and phase
- What is the input-output phase shift for very high frequencies?
- Identify the range of frequencies corresponding to the midband operation.
- Identify the frequency points with the largest approximation errors for magnitude and the phase, respectively.

Sol.:  $s^2 + 1001s + 1000 = 0 \Rightarrow \begin{cases} p_1 + p_2 = -1001 \\ p_1 \cdot p_2 = 1000 \end{cases} \Rightarrow$

$\Rightarrow p_1 = -1$   
 $p_2 = -1000$

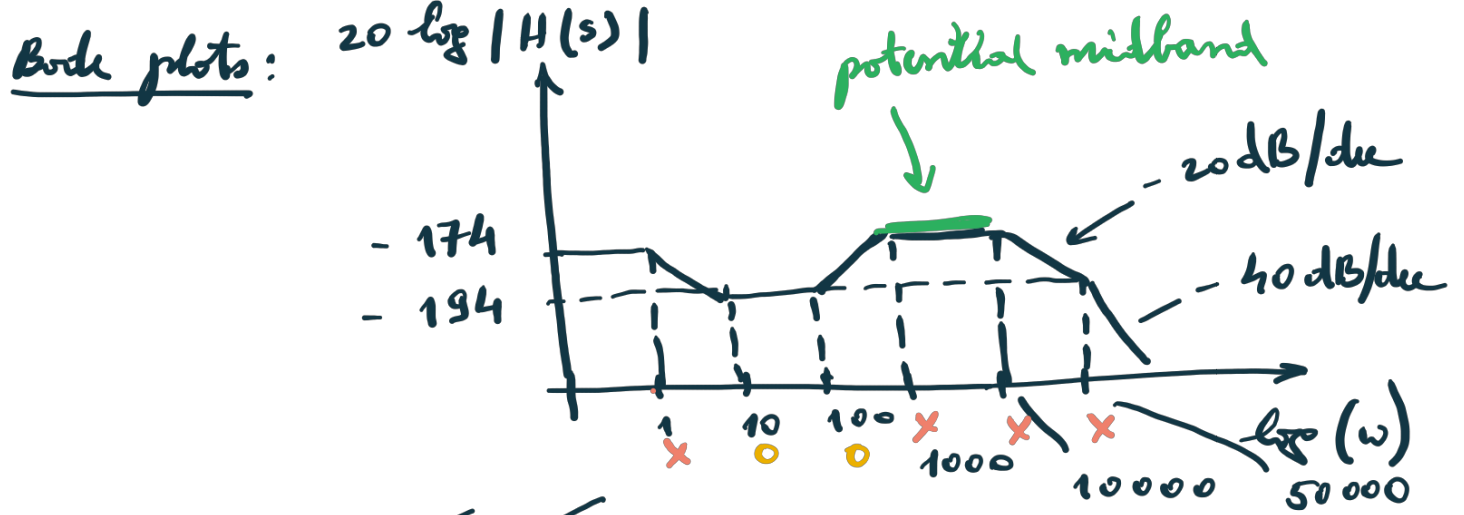
$z_1 = -10, z_2 = -100$

$$H(s) = \frac{(s+10)(s+100)}{(s+1)(s+1000)(s+10000)(s+50000)}$$

$\hookrightarrow p_1 = -1, p_2 = -1000,$   
 $p_3 = -10000, p_4 = -50000$

$\omega_{z1} = 10 \text{ rad/s}, \omega_{z2} = 100 \text{ rad/s}$

$\omega_{p1} = 1 \text{ rad/s}, \omega_{p2} = 1000, \omega_{p3} = 10000 \text{ rad/s},$   
 $\omega_{p4} = 50,000 \text{ rad/s}$

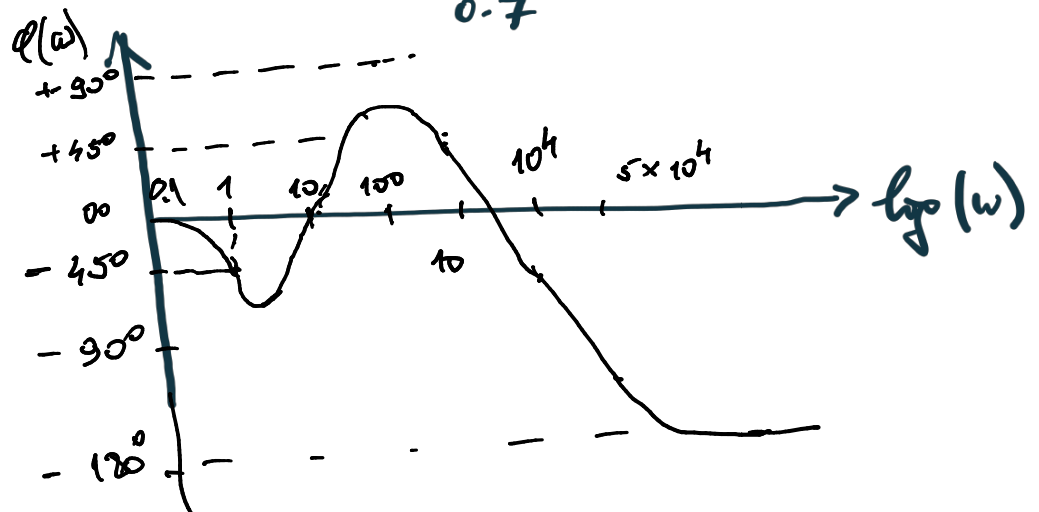


$$H_{DC} = H(0) = \frac{10 \cdot 100}{1 \cdot 10^3 \cdot 10^4 \cdot 5 \cdot 10^4} = \frac{1}{5} \cdot 10^{-8}$$

$$20 \lg |H(0)| = 20 (-8 - \lg 5) \approx -174 \text{ dB}$$

$\lg 5 \approx 0.7$

Phase plot



(b) for  $w \geq 10 \times 5 \cdot 10^4$ , the phase shift

$$\phi(w) = -180^\circ$$

(c) Midband operation corresponds to a flat region in the magnitude response.

Such a region is for  $1000 \text{ rad/s} \leq w \leq 10000 \text{ rad/s}$

d) Max error points:

- for  $|H(jw)| \rightarrow$  at the critical frequencies  
 $w = 1, 10, 100, 1000, 10000, 50000 \text{ rad/s}$

— for phase  $Q(\omega)$  — one decade below and  
one decade above the poles/zeros frequencies

$$\omega = 0.1, 1, 10, 100, 1000, 5000, \\ 10000, 100000, 500000 \text{ rad/s}$$

Grading: 25p total

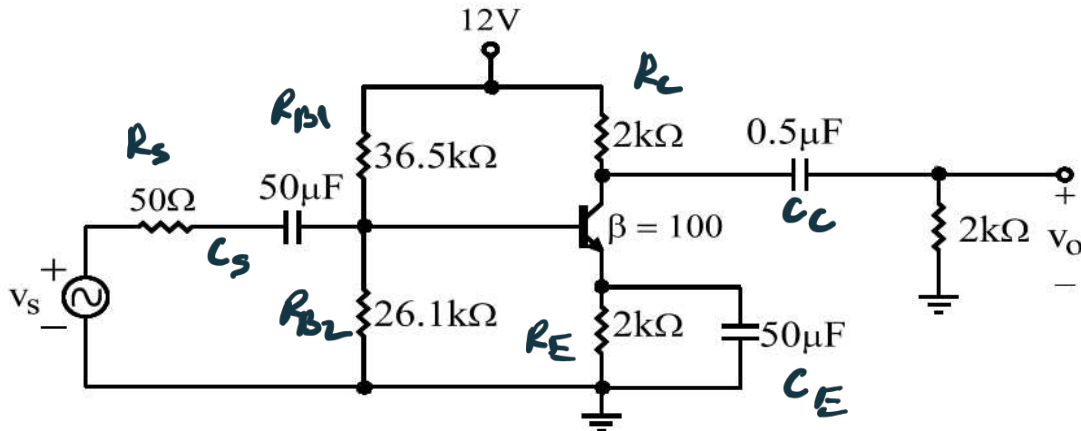
a) 10p - 5p Bode magnitude + 5p Bode phase

b) 5p - phase shift at very high freq = -180deg

c) 5p - identifying a flat region for midband operation

d) 5p - 2.5p for frequency values with max error on magnitude plot + 2.5p for frequency values with max error for phase plot

3) [25p] For the circuit below:



The npn transistor has the parameters  $\beta=100$ ,  $C_\pi=10\text{pF}$ ,  $C_\mu=2\text{pF}$ ,  $r_o=\infty$

- Determine (with approximation) the quiescent operating point of the transistor
- Compute the small signal parameters and draw the small signal equivalent model
- Draw the low frequency circuit, the midband circuit and the high frequency circuit
- Compute the midband voltage gain  $v_o/v_s$  of the amplifier stage
- Compare the advantages and disadvantages of BJT and MOS transistors. When would you prefer BJTs instead of MOS transistors?

Sol:

a) The quiescent point:

$$V_B \approx \frac{R_{B2}}{R_{B1} + R_{B2}} V_{CC} \quad (\text{assume } I_{B2} \gg I_B)$$

$$V_B = \frac{26.1}{26.1 + 36.5} 12\text{V} = \frac{26.1}{62.6} 12\text{V} = 0.417 \cdot 12\text{V} = 5\text{V}$$

$$I_E = \frac{V_B - 0.7\text{V}}{R_E} = \frac{4.3\text{V}}{2\text{k}\Omega} = 2.15\text{mA} \Rightarrow I_B = \frac{2.15\text{mA}}{101} = 21.3\mu\text{A}$$

$$I_{B2} = \frac{V_B}{R_{B2}} = \frac{5\text{V}}{26.1\text{k}\Omega} = 192\mu\text{A} \gg I_B = 21.3\mu\text{A}$$

(or otherwise you can iterate the computation, for enhanced accuracy)

$$I_C = I_E - I_B \approx 2.13\text{mA}$$

$$V_C = V_{CC} - R_C I_C = 12\text{V} - 2\text{k}\Omega \cdot 2.13\text{mA} = 12\text{V} - 4.26\text{V} = 7.74\text{V}$$

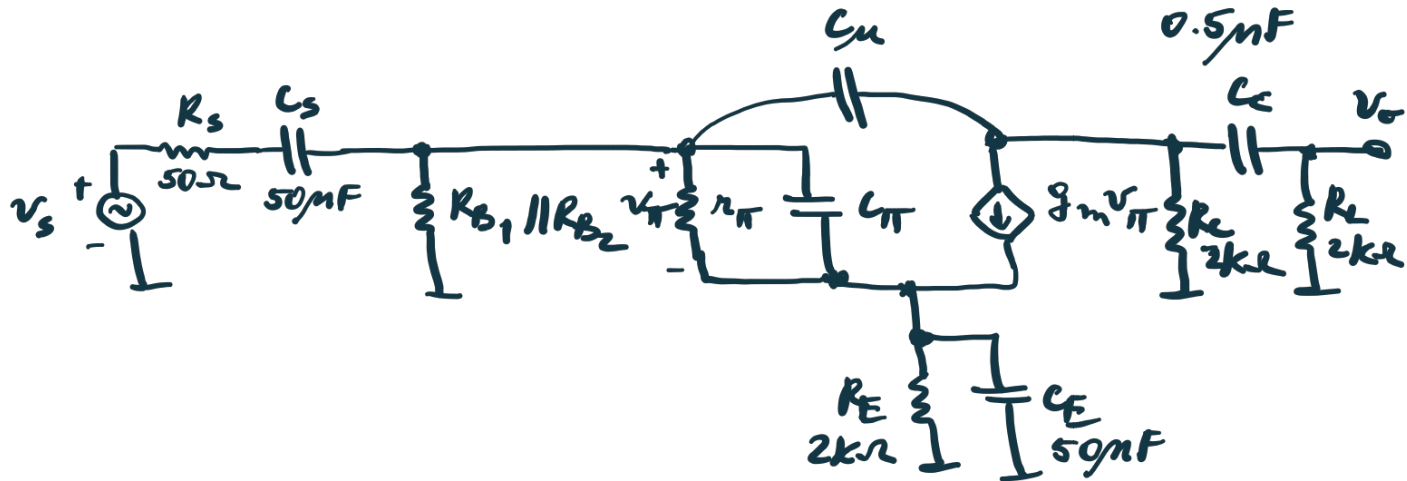
$V_C > V_B \Rightarrow$  CB junction is reverse biased  $\Rightarrow$  BJT is biased in the normal active mode

$$\begin{cases} V_B = 5\text{V}, V_C = 7.74\text{V}, V_E = 4.3\text{V}, V_{CE} = 3.44\text{V} \\ I_C = 2.13\text{mA}, I_B = 21.3\mu\text{A} \end{cases}$$

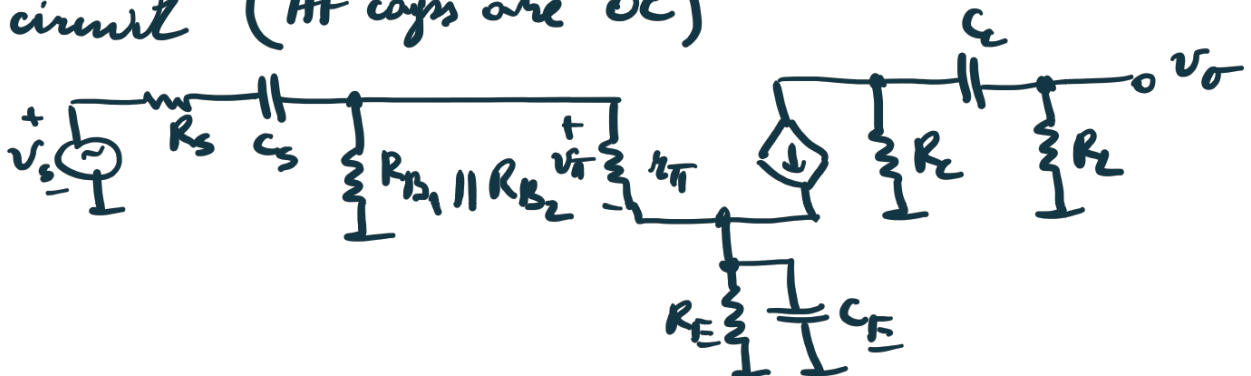
b) Small signal parameters:  $g_m = \frac{I_c}{V_T} \approx \frac{2.13 \text{ mA}}{25 \text{ mV}} = 85.2 \text{ mA/V}$

$$r_{\pi} = \frac{\beta}{g_m} = \frac{100}{85.2} \text{ k}\Omega = 1.17 \text{ k}\Omega$$

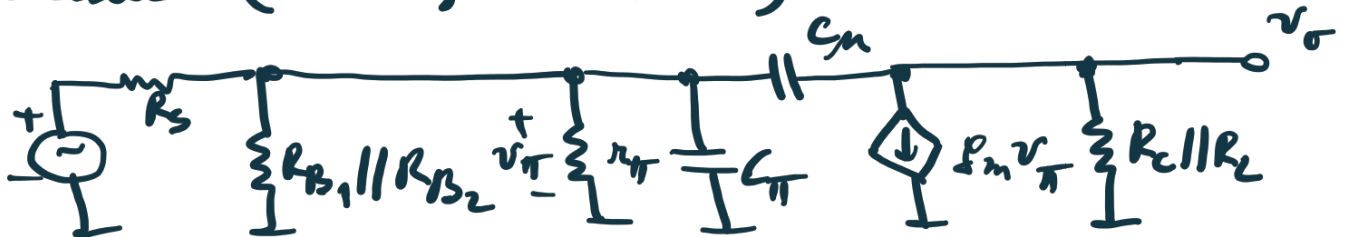
The small signal equiv:



c)  $C_s, C_c, C_E$  = LF capacitors  
 $C_{\pi}, C_{\mu}$  = HF capacitors  
 LF circuit (HF caps are OC)



HF circuit (LF caps are SC)



Midband small signal circuit





Midband voltage gain:

$$v_o = -g_m v_{\pi} R_c \parallel R_L = -g_m (R_c \parallel R_L) \cdot \frac{R_{BB}}{R_s + R_{\pi} \parallel R_{BB}} v_s$$

$$A_v = \frac{v_o}{v_s} = -g_m (R_c \parallel R_L) \frac{R_{BB}}{R_s + R_{\pi} \parallel R_{BB}}$$

$$R_c \parallel R_L = 2k\Omega \parallel 2k\Omega = 1k\Omega$$

$$R_{\pi} = 1.17k\Omega$$

$$g_m = 85.2 \text{ mA/V}$$

$$R_{BB} = R_{B1} \parallel R_{B2} = 36.5k\Omega \parallel 26.1k\Omega = \frac{36.5 \times 26.1}{62.6} k\Omega = 15.22k\Omega$$

$$R_{\pi} \parallel R_{BB} = 1.17k\Omega \parallel 15.22k\Omega \approx R_{\pi}$$

$$\frac{1.17 \cdot 15.22}{16.39} = 1.09k\Omega$$

$$A_v = \frac{v_o}{v_s} = -85.2 \cdot 10^{-3} \Omega^{-1} \cdot 10^3 \Omega \cdot \frac{1.09}{0.05 + 1.09}$$

$$A_v = -85.2 \cdot \frac{1.09}{1.14} = -85.2 \cdot 0.96 = -81.5$$

(e) BJT vs MOS transistors

- BJT can provide higher (current) gains  
+ lower noise levels for low frequency
- MOS provide much higher input impedance

BJT are for instance preferred for high-power output stages (e.g. class B output audio stages)  
(they can also have lower output impedance)

Grading: 25p in total

a) 5p - quiescent operating point:  $I_C$ ,  $V_{CE}$ ,  $I_B$

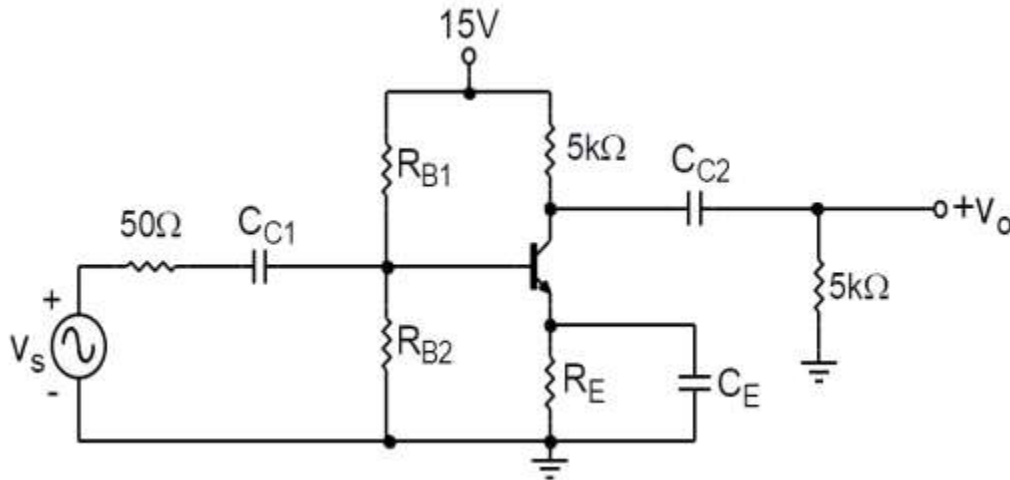
b) 5p - small signal model and parameters

c) 6p - 2p (LF circuit), 2p (midband circuit), 2p (HF circuit)

d) 5p  $A_v$  in midband

e) 4p - BJT vs MOS

- 4) [25p] For the circuit shown in the figure, the transistor has the parameters  $\beta=100$ ,  $r_o=\infty$ :



- 7.5p  
10p  
7.5p
- Use one of the  $1/3^{\text{rd}}$  rules to bias the circuit and determine the values for  $R_{B1}$ ,  $R_{B2}$ ,  $R_E$
  - Determine the midband voltage gain, with and without the capacitor  $C_E$  being present
  - Determine the input and output impedances of the amplifier stage in the midband range, with and without  $C_E$ .

Sol: first  $1/3$  rule:

$$V_B = \frac{1}{3} V_{CC}$$

$$V_C = \frac{2}{3} V_{CC}$$

$$I_1 = \frac{I_E}{\sqrt{\beta}} \text{ or } I_1 = 0.1 I_E$$

2nd  $1/3$  rule:

$$V_E = \frac{1}{3} V_{CC}$$

$$V_C = \frac{2}{3} V_{CC}$$

$$I_1 = \frac{I_E}{\sqrt{\beta}} \text{ or } I_1 = 0.1 I_E$$

choose for instance the 2nd form of  $1/3$  rule:

$$V_E = \frac{1}{3} V_{CC} = 5V \Rightarrow V_B = 5.7V \quad (V_{BE} = 0.7V)$$

$$V_C = \frac{2}{3} V_{CC} = 10V, \quad V_{CE} = 5V$$

Select  $I_C$  to achieve a desired  $g_m$  ( $g_m = \frac{I_C}{V_T} = \frac{I_C}{25mV}$ )

in our case  $R_C = 5k\Omega \Rightarrow I_C = \frac{5V}{5k\Omega} = 1mA$

$$g_m = \frac{I_C}{V_T} = \frac{1000}{25} \text{ mA/V}$$

$$\boxed{g_m = 40 \text{ mA/V}}$$

$$I_E \approx I_C = 1mA$$

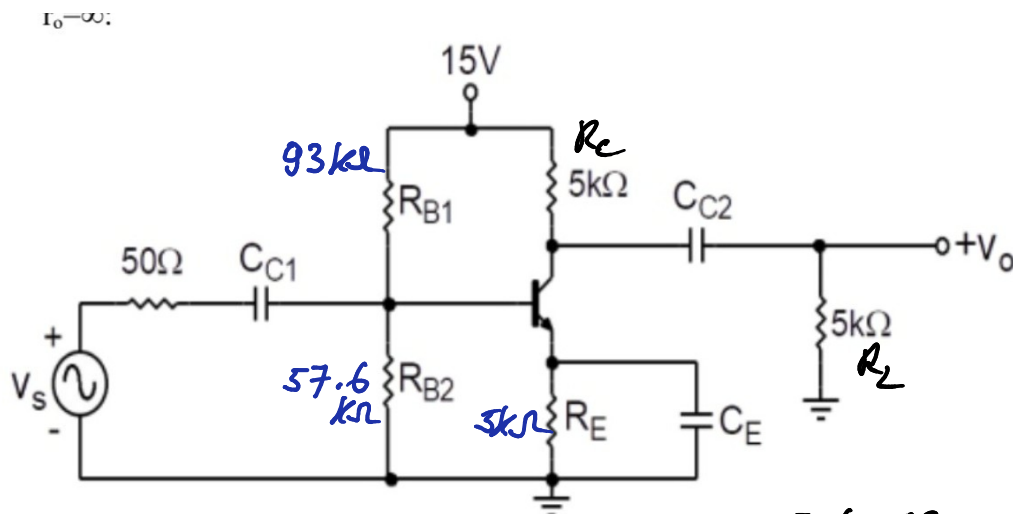
$$I_B = \frac{1mA}{100} = 10\mu A$$

$$V_E = \frac{1}{3} V_{CC} = 5V \Rightarrow R_E \approx R_C = 5k\Omega$$

$$\text{Set } \dot{I}_1 = 0.1 \dot{I}_E = 0.1 \text{ mA}$$

$$R_{B1} = \frac{V_{CC} - V_B}{\dot{I}_1} = \frac{15V - 5.7V}{0.1 \text{ mA}} = \frac{9.3V}{0.1 \text{ mA}} = 93k\Omega$$

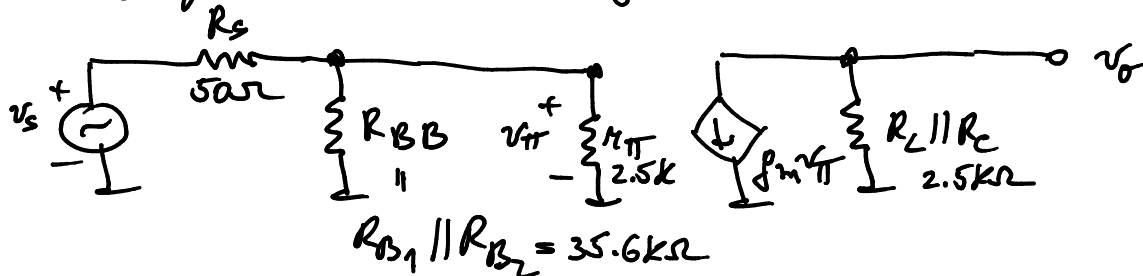
$$R_{B2} = \frac{V_B}{\dot{I}_1 - \dot{I}_B} = \frac{5.7V}{0.1 \text{ mA} - 0.01 \text{ mA}} = \frac{5.7V}{0.09 \text{ mA}} = 57.6k\Omega$$



$$R_{BB} = R_{B1} \parallel R_{B2} = \frac{57.6 \times 93}{150.6} = 35.6k\Omega$$

(b) Midband gain  
# with  $C_E$  present:

$$r_{\pi} = \frac{\beta}{g_m} = \frac{100}{40} \cdot \frac{1}{10} \Omega = 2.5k\Omega$$

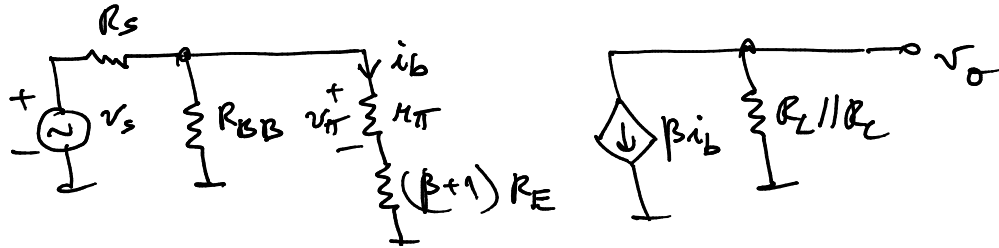
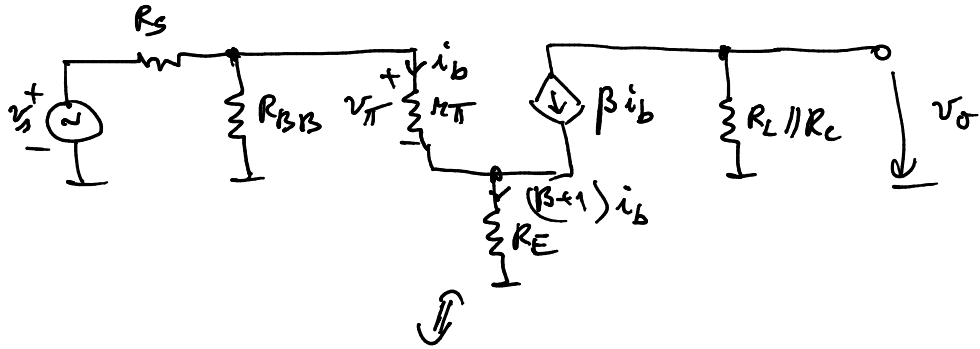


$$v_o = -g_m (R_L \parallel R_C) v_{\pi} = -g_m (R_L \parallel R_C) \cdot \frac{r_{\pi} \parallel R_{BB}}{R_s + r_{\pi} \parallel R_{BB}} v_s$$

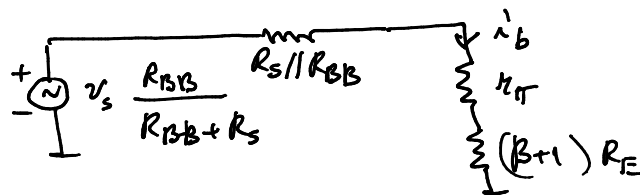
$$A_v \Big|_{C_E \rightarrow \infty} = -g_m (R_L \parallel R_C) \frac{r_{\pi} \parallel R_{BB}}{R_s + (r_{\pi} \parallel R_{BB})}$$

$$A_v = -40 \cdot 10^{-3} \cdot 2.5 \cdot 10^3 \cdot \frac{2.5k \parallel 35.6k}{50 + 2.5k \parallel 35.6k} \approx -100 \text{ V/V}$$

# Without  $C_E$



$$v_o = -\beta (R_L \parallel R_C) i_b$$



$$i_b = v_s \frac{R_{BB}}{R_{BB} + R_s} \cdot \frac{1}{R_s \parallel R_{BB} + r_{\pi} + (\beta + 1) R_E}$$

$$v_o \Big|_{R_E} = -\beta (R_L \parallel R_C) \frac{R_{BB}}{R_{BB} + R_s} \cdot \frac{1}{R_s \parallel R_{BB} + r_{\pi} + (\beta + 1) R_E} v_s$$

$$A_v \Big|_{C_E \rightarrow 0} = -\beta \underbrace{(R_L \parallel R_C)}_{100} \underbrace{\frac{R_{BB}}{R_{BB} + R_s}}_{2.5k\Omega} \cdot \frac{1}{\underbrace{R_s \parallel R_{BB} + r_{\pi}}_{35.6k\Omega} + \underbrace{(\beta + 1) R_E}_{35.6k\Omega + 50\Omega + 101 \cdot 5k\Omega}}$$

$$A_v \Big|_{C_E \rightarrow 0} = -100 \cdot \frac{2.5}{505 + 35.6 + 2.5} = -100 \frac{2.5}{543.1} = -0.5$$

# (c)  $R_{in}$ ,  $R_{out}$  :

(c1)  $C_E \rightarrow \infty \Rightarrow R_{in} = R_{BB} \parallel r_{\pi} = 35.6k\Omega \parallel 2.5k\Omega \approx r_{\pi} = 2.5k\Omega$

$R_{out} = R_C$  (not including  $R_L$ ) =  $5k\Omega$

(c2)  $C_E \rightarrow 0 \Rightarrow R_{in} = R_{BB} \parallel (r_{\pi} + (\beta + 1) R_E) = 35.6k\Omega \parallel 507.5k\Omega \approx R_{BB} = 35.6k\Omega$

Grading: 25p in total

- a) 7.5p - bias computation - 2.5p for each RE, RB1, RB2
- b) 10p - 5p  $A_v$  with CE + 5p  $A_v$  without CE
- c) 7.5p - 3p  $R_{in}, R_{out}$  with CE, 4.5p  $R_{in}, R_{out}$  without CE